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MICROWAVE POWER GAN HEMT TGI9098-100P

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

·INTERNALLY MATCHED HEMT

·HIGH POWER

Pout= 50.0dBm at Pin= 42dBm

·HIGH GAIN

GL= 12.0dB at 9.0GHz to 9.8GHz

·HERMETICALLY SEALED PACKAGE

•PULSE OPERATION

Pulse width=100µs, Duty cycle=10%



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power (pulsed)	Pout	VDS= 24V IDSset= 6A f= 9.0 to 9.8 GHz @Pin= 42dBm Pulse width=100µs Duty cycle=10%	dBm	49.0	50.0	
Drain Current (pulsed)	IDS1		А	_	10.0	13.0
Power Added Efficiency	ηadd		%		40	
Linear Gain	GL	@Pin= 35dBm	dB		12.0	

Recommended Gate Resistance(Rg): 10 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 10.0A	S		9	
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 46mA	V	-1	-4	-6
Gate-Source Breakdown Voltage	VGSO	IGS= -20mA	V	-10	_	_
Thermal Resistance	Rth(c-c)	Channel to Case(*)	°C/W		0.8	

(*) measured at CW condition

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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING	
Drain-Source Voltage	VDS	V	50	
Gate-Source Voltage	VGS	V	-10	
Drain Current	IDS	А	22.5	
Total Power Dissipation (Tc= 25°C)	PT	W	280	
Channel Temperature	Tch	°C	250	
Storage Temperature	Tstg	°C	-65 to +175	

PACKAGE OUTLINE (7-AA03A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

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MICROWAVE POWER GaN HEMT **TGI9098-100P**

TYPICAL RF PERFORMANCE

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

Pout , PAE vs. Pin





·Rth(c-c) vs. Pulse Width



Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.